NSN 5961-01-322-1718

Diode Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-322-1718 **Inclosure Material:** Metal **Overall Length:** 1.000 inches **Function For Which Designed:** Rectifier **End Application:** Low altitute navigation & targeting infrared system (lantirn) **Mounting Facility Quantity: Mounting Method:** Threaded stud **Features Provided:** Burn in and hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Criticality Code Justification:** Feat **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 500.0 reverse voltage, peak **Current Rating Per Characteristic:** 300.00 amperes forward current, average preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Weapon system essential; junction pattern arrangement: pn **Test Data Document:** 04939-717801309 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 pin Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

NSN 5961-01-322-1718

Diode Semiconductor Device - Page 2 of 2



Fiig:

A110a0